

**SEMICONDUCTOR DEVICE
AND
METHOD OF MANUFACTURING THE SAME**

5

ABSTRACT OF THE DISCLOSURE

The present invention improves the aperture ratio of a pixel of a reflection-type display device or a reflection type display device without increasing the number of masks and without using a blackmask. A pixel electrode (167) is arranged so as to partially overlap a source wiring (137) for shielding the gap between pixels from light, and a thin film transistor is arranged so as to partially overlap a gate wiring (166) for shielding a channel region of the thin film transistor from light, thereby realizing a high pixel aperture ratio.

15 (Fig. 5)